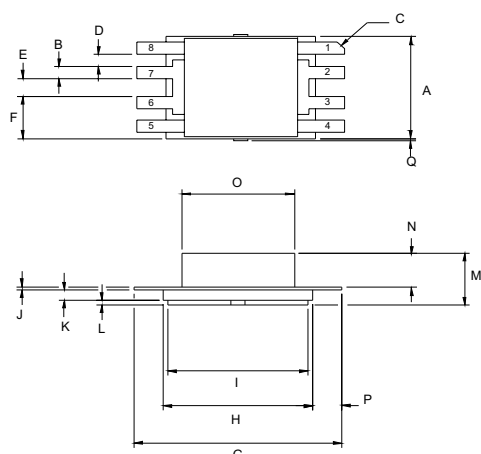


MECHANICAL DATA



DBC1 Package

PIN 1 Source	PIN 5 Source
PIN 2 Drain	PIN 6 Gate
PIN 3 Drain	PIN 7 Gate
PIN 4 Source	PIN 8 Source

DIM	mm	Tol.	Inches	Tol.
A	6.47	0.08	.255	.003
B	0.76	0.08	.030	.003
C	45°	5°	45°	5°
D	0.76	0.08	.030	.003
E	1.14	0.08	.045	.003
F	2.67	0.08	.105	.003
G	11.73	0.13	.462	.005
H	8.43	0.08	.332	.003
I	7.92	0.08	.312	.003
J	0.20	0.02	.008	.001
K	0.64	0.02	.025	.001
L	0.30	0.02	.012	.001
M	3.25	0.08	.128	.003
N	2.11	0.08	.083	.003
O	6.35SQ	0.08	.250SQ	.003
P	1.65	0.51	.065	.020
Q	0.13	max	.005	max

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 10W – 7.2V – 1GHz SINGLE ENDED

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- LOW NOISE
- HIGH GAIN

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1 MHz to 2 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	70W
BV_{DSS}	Drain – Source Breakdown Voltage	40V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	16A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 10mA	40			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 12.5V V _{GS} = 0			8	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			8	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 0.8A	1.44			S
G _{PS} Common Source Power Gain	P _O = 10W	7			dB
η Drain Efficiency	V _{DS} = 7.2V I _{DQ} = 0.8A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 0 V _{GS} = –5V f = 1MHz			96	pF
C _{oss} Output Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			80	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			8	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 2.5°C / W
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